MSKSEMI 美森科













ESD

T\/9

TSS

MOV

GDT

PIFD

MJD127T4G(MS)

Product specification





TRANSISTOR (PNP)

FEATURES

- High DC Current Gain
- Electrically Similar to Popular TIP127
- Built-in a Damper Diode at E-C

Reference News

PACKAGE OUTLINE		Pin Configuration	Marking	
3 2	1.BASE 2.COLLECTOR 3.EMITTER	Book of the state	MSKSEMI MJD127T4G MS XXX	

MAXIMUM RATINGS (Ta=25 ℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
Vcво	Collector-Base Voltage	-100	V
Vceo	Collector-EmitterVoltage	-100	V
V _{EBO}	Emitter-Base Voltage	-5	V
lc	Collector Current -Continuous	-8	А
Pc	Collector Power Dissipation	1.5	W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55-150	°C



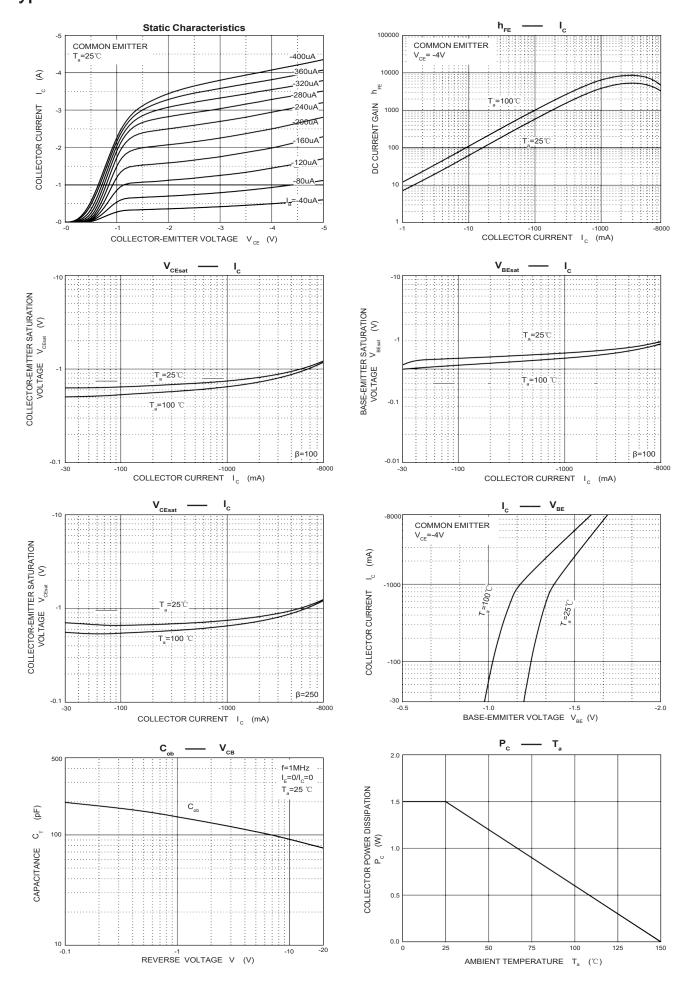
ELECTRICAL CHARACTERISTICS (T₂=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-1mA,I _E =0	-100			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-30mA,I _B =0	-100			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-10mA,I _C =0	-5			V
Collector cut-off current	Ісво	V _{CB} =-100V,I _E =0			-10	μA
Collector-emitter cut-off current	ICEO	Vc=-50V,IB=0			-10	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V,I _C =0			-2	mA
DC current gain	h _{FE(1)}	V _{CE} =-4V,I _C =-4A	1000		12000	
50 carroin gain	h _{FE(2)}	V _{CE} =-4V,I _C =-8A	100			
Collector-emitter saturation voltage	VCE(sat) 1*	I _C =-4A,I _B =-16mA			-2	V
Solicotor clinicor saturation voltage	VCE(sat) 2*	I _C =-8A,I _B =-80mA			-4	V
Base-emitter saturation voltage	V _{BE(sat)} *	I _C =-8A,I _B =-80mA			-4.5	V
Base-emitter voltage	V _{BE}	V _{CE} =-4V,I _C =-4A			-2.8	V
Collector output capacitance	Cob	V _{CB} =-10V,I _E =0,f=0.1MHz			300	pF

^{*}Pulse Test: Pulse Width≤380µs, Duty Cycle≤2%

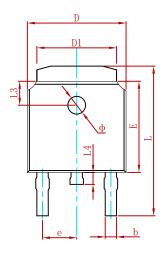


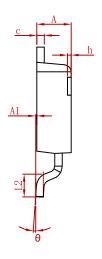
TypicalCharacteristics

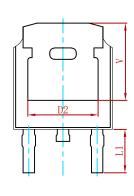




PACKAGE MECHANICAL DATA

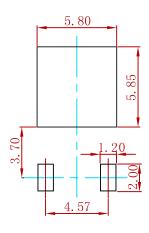






	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.635	0.770	0.025	0.030	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.830 REF.		0.190	REF.	
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.712	10.312	0.382	0.406	
L1	2.900 REF.		0.114 REF.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 REF.		0.063	REF.	
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.250 REF.		0.207	REF.	

Suggested Pad Layout



Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
MJD127T4G(MS)	TO-252	2500



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